

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes first to M-th semiconductor dies stacked in a first direction. Each of the first to M-th semiconductor dies includes a substrate, first to K-th through silicon vias passing through the substrate in the first direction, and a first circuit to receive power through a power supply line electrically connected to the first through silicon via. Each of first to K-th through silicon vias of the N-th semiconductor die is electrically connected to a through silicon via of first to K-th through silicon vias of the (N+1)-th semiconductor die that is spaced apart therefrom in a plan view.

FIG. 1